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Erratum: “A GaN–SiC hybrid material for high-frequency and power electronics” [Appl. Phys. Lett. 113, 041605 (2018)] **FREE**

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Erratum: “A GaN–SiC hybrid material for high-frequency and power electronics” [Appl. Phys. Lett. 113, 041605 (2018)]

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The figure number for Figs. 3(d) and 3(e) is labeled incorrectly on page 3 in the original article.¹ The correct figure number is shown in the sentence below.

Moreover, a closer look at the GaN/AlN interface and the AlN/SiC interface, as shown in Figs. 3(d) and 3(e), respectively, reveals that the lattice mismatch between GaN and SiC can be well accommodated with the periodic

misfits at the GaN/AlN interface, given that a part of the strain is released inevitably through the generation of threading dislocations.

¹J.-T. Chen, J. Bergsten, J. Lu, E. Janzen, M. Thorsell, L. Hultman, N. Rorsman, and O. Kordina, “A GaN–SiC hybrid material for high-frequency and power electronics,” *Appl. Phys. Lett.* **113**, 041605 (2018).

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